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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/687,271
				Filing Date	October 16, 2003
				First Named Inventor	Olubunmi O. Adetunji et al.
				Group Art Unit	2813
				Examiner Name	Laura M. Schillinger
				Attorney Docket Number	SC12752TP
Sheet	1	of	1		

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

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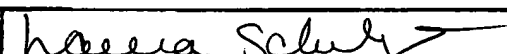
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Sheet		of	Attorney Docket Number	SC12752TP

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	BH	Byeong-Ok Cho <i>et al.</i> , "Tuning the Electrical Properties of Zirconium Oxide Thin Films," <i>Applied Physics Letters</i> , February 11, 2002, Vol. 80, No. 6, pp. 1052-1054.	
	BI	A. L. P. Rotondaro, <i>et al.</i> , "Advanced CMOS Transistors with a Novel HfSiON Gate Dielectric," <i>2002 Symposium on VLSI Technology Digest of Technical Papers</i> , Section 15.2.	
	BJ	Yuji Saito, <i>et al.</i> , "Advantage of Radical Oxidation for Improving Reliability of Ultra-Thin Gate Oxide," <i>2002 Symposium on VLSI Technology Digest of Technical Papers</i> .	
	BK	M. Togo, <i>et al.</i> , "Low-Leakage and Highly-Reliable 1.5 nm SiON Gate-Dielectric Using Radical Oxynitridation for Sub-0.1 μ m CMOS," <i>2000 Symposium on VLSI Technology Digest of Technical Papers</i> .	

Examiner Signature		Date Considered	1/22/06
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Group Art Unit

Examiner Name _____

Attorney Docket Number

Rate If Known	Rate If Not Known
10/687 2.71	

Concurrently Herewith 10/16/03

Olubunmi O. Adetutu

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AL	AA	Al-Shareef <i>et al.</i> , "Device Performance of <i>in-situ</i> Steam Generated Gate Dielectric Nitrided by Remote Plasma Nitridation," <i>Applied Physics Letters</i> , June 11, 2001, Vol. 78, No. 24, pp. 3875-3877/	
V	AB	Nicollian <i>et al.</i> , "Extending Reliability Scaling Limit of SiO ₂ Through Plasma Nitridation," <i>IEDM Tech. Dig.</i> , 2000, pp. 545-548.	
AL	AC	Tseng <i>et al.</i> , "Ultra-Thin Decoupled Plasma Nitridation (DPN) Oxynitride Gate Dielectric for 80-nm Advanced Technology," <i>IEEE Electron Device Letters</i> , December 2002, Vol. 23, No. 12, pp. 704-706.	

**Examiner
Signature**

hanna Solberg

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